

Emanuel Tutuc

List of Publications by Year in descending order

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all docs

150
docs citations

150
times ranked

24530
citing authors

#	ARTICLE	IF	CITATIONS
1	Large-Area Synthesis of High-Quality and Uniform Graphene Films on Copper Foils. <i>Science</i> , 2009, 324, 1312-1314.	12.6	10,000
2	The Role of Surface Oxygen in the Growth of Large Single-Crystal Graphene on Copper. <i>Science</i> , 2013, 342, 720-723.	12.6	977
3	Evidence for moiré excitons in van der Waals heterostructures. <i>Nature</i> , 2019, 567, 71-75.	27.8	933
4	Realization of a high mobility dual-gated graphene field-effect transistor with Al ₂ O ₃ dielectric. <i>Applied Physics Letters</i> , 2009, 94, .	3.3	827
5	Field-effect transistors and intrinsic mobility in ultra-thin MoSe ₂ layers. <i>Applied Physics Letters</i> , 2012, 101, .	3.3	494
6	van der Waals Heterostructures with High Accuracy Rotational Alignment. <i>Nano Letters</i> , 2016, 16, 1989-1995.	9.1	477
7	Tunable moiré bands and strong correlations in small-twist-angle bilayer graphene. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2017, 114, 3364-3369.	7.1	434
8	Hubbard Model Physics in Transition Metal Dichalcogenide Moiré Bands. <i>Physical Review Letters</i> , 2018, 121, 026402.	7.8	413
9	Spectrally selective chiral silicon metasurfaces based on infrared Fano resonances. <i>Nature Communications</i> , 2014, 5, 3892.	12.8	397
10	Topological Insulators in Twisted Transition Metal Dichalcogenide Homobilayers. <i>Physical Review Letters</i> , 2019, 122, 086402.	7.8	333
11	Counterflow Measurements in Strongly Correlated GaAs Hole Bilayers: Evidence for Electron-Hole Pairing. <i>Physical Review Letters</i> , 2004, 93, 036802.	7.8	273
12	The marvels of moiré materials. <i>Nature Reviews Materials</i> , 2021, 6, 201-206.	48.7	262
13	High-Mobility Holes in Dual-Gated WSe ₂ Field-Effect Transistors. <i>ACS Nano</i> , 2015, 9, 10402-10410.	14.6	232
14	Photonic-crystal exciton-polaritons in monolayer semiconductors. <i>Nature Communications</i> , 2018, 9, 713.	12.8	197
15	Flat bands in twisted bilayer transition metal dichalcogenides. <i>Nature Physics</i> , 2020, 16, 1093-1096.	16.7	197
16	Correlated Insulating States in Twisted Double Bilayer Graphene. <i>Physical Review Letters</i> , 2019, 123, 197702.	7.8	194
17	Bilayer PseudoSpin Field-Effect Transistor (BiSFET): A Proposed New Logic Device. <i>IEEE Electron Device Letters</i> , 2009, 30, 158-160.	3.9	193
18	Structural and Electrical Properties of MoTe ₂ and MoSe ₂ Grown by Molecular Beam Epitaxy. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 7396-7402.	8.0	189

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19	Topologically Protected Helical States in Minimally Twisted Bilayer Graphene. <i>Physical Review Letters</i> , 2018, 121, 037702.	7.8	175
20	Field Effect Transistors with Current Saturation and Voltage Gain in Ultrathin ReS ₂ . <i>ACS Nano</i> , 2015, 9, 363-370.	14.6	169
21	Air Stable Doping and Intrinsic Mobility Enhancement in Monolayer Molybdenum Disulfide by Amorphous Titanium Suboxide Encapsulation. <i>Nano Letters</i> , 2015, 15, 4329-4336.	9.1	167
22	Gate-Tunable Resonant Tunneling in Double Bilayer Graphene Heterostructures. <i>Nano Letters</i> , 2015, 15, 428-433.	9.1	166
23	Coulomb drag of massless fermions in graphene. <i>Physical Review B</i> , 2011, 83, .	3.2	165
24	Resistance Spikes at Transitions Between Quantum Hall Ferromagnets. , 2000, 290, 1546-1549.		148
25	Valley Splitting of AAs Two-Dimensional Electrons in a Perpendicular Magnetic Field. <i>Physical Review Letters</i> , 2002, 89, 226805.	7.8	138
26	Band Alignment in WSe ₂ Graphene Heterostructures. <i>ACS Nano</i> , 2015, 9, 4527-4532.	14.6	138
27	Shubnikova de Haas Oscillations of High-Mobility Holes in Monolayer and Bilayer WSe_2 Landau Level Degeneracy, Effective Mass, and Negative Compressibility. <i>Physical Review Letters</i> , 2016, 116, 086601.	7.8	137
28	Band Offset and Negative Compressibility in Graphene-MoS ₂ Heterostructures. <i>Nano Letters</i> , 2014, 14, 2039-2045.	9.1	134
29	Chemical potential and quantum Hall ferromagnetism in bilayer graphene. <i>Science</i> , 2014, 345, 58-61.	12.6	120
30	Interlayer exciton laser of extended spatial coherence in atomically thin heterostructures. <i>Nature</i> , 2019, 576, 80-84.	27.8	120
31	Two-dimensional electrons occupying multiple valleys in AAs. <i>Physica Status Solidi (B): Basic Research</i> , 2006, 243, 3629-3642.	1.5	109
32	CMOS-Compatible Synthesis of Large-Area, High-Mobility Graphene by Chemical Vapor Deposition of Acetylene on Cobalt Thin Films. <i>ACS Nano</i> , 2011, 5, 7198-7204.	14.6	109
33	Reconfigurable Complementary Monolayer MoTe ₂ Field-Effect Transistors for Integrated Circuits. <i>ACS Nano</i> , 2017, 11, 4832-4839.	14.6	108
34	Scaling of Al ₂ O ₃ dielectric for graphene field-effect transistors. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	105
35	Strongly Enhanced Tunneling at Total Charge Neutrality in Double-Bilayer Graphene- WSe_2 Heterostructures. <i>Physical Review Letters</i> . 2018. 120. 177702.	7.8	102
36	In-Plane Magnetic Field-Induced Spin Polarization and Transition to Insulating Behavior in Two-Dimensional Hole Systems. <i>Physical Review Letters</i> , 2001, 86, 2858-2861.	7.8	99

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37	Dielectric thickness dependence of carrier mobility in graphene with HfO ₂ top dielectric. Applied Physics Letters, 2010, 97, .	3.3	97
38	Spin Susceptibility of Two-Dimensional Electrons in Narrow AlAs Quantum Wells. Physical Review Letters, 2004, 92, 226401.	7.8	93
39	Spin Polarization and g Factor of a Dilute GaAs Two-Dimensional Electron System. Physical Review Letters, 2002, 88, 036805.	7.8	91
40	Experimental Demonstration of Phase Modulation and Motion Sensing Using Graphene-Integrated Metasurfaces. Nano Letters, 2016, 16, 3607-3615.	9.1	84
41	Realization of a Linear Germanium Nanowire p-n Junction. Nano Letters, 2006, 6, 2070-2074.	9.1	81
42	High performance wire-array silicon solar cells. Progress in Photovoltaics: Research and Applications, 2011, 19, 307-312.	8.1	79
43	Direct Measurement of the Fermi Energy in Graphene Using a Double-Layer Heterostructure. Physical Review Letters, 2012, 108, 116404.	7.8	77
44	Radial modulation doping in core-shell nanowires. Nature Nanotechnology, 2014, 9, 116-120.	31.5	76
45	Density-Dependent Quantum Hall States and Zeeman Splitting in Monolayer and Bilayer WS_2 . Physical Review Letters, 2017, 118, 247701.	7.8	72
46	Large effective mass and interaction-enhanced Zeeman splitting of K -valley electrons in $MoSe_2$. Physical Review B, 2018, 97, .	3.2	72
47	Atomistic simulation of the electronic states of adatoms in monolayer MoS ₂ . Applied Physics Letters, 2014, 104, .	3.3	66
48	Doping of germanium nanowires grown in presence of PH ₃ . Applied Physics Letters, 2006, 89, 263101.	3.3	65
49	Low-Frequency Acoustic Phonon Temperature Distribution in Electrically Biased Graphene. Nano Letters, 2011, 11, 85-90.	9.1	63
50	Enhanced electron mobility and high order fractional quantum Hall states in AlAs quantum wells. Applied Physics Letters, 2002, 80, 1583-1585.	3.3	60
51	Giant Frictional Drag in Double Bilayer Graphene Heterostructures. Physical Review Letters, 2016, 117, 046803.	7.8	58
52	Highly valley-polarized singlet and triplet interlayer excitons in van der Waals heterostructure. Physical Review B, 2019, 100, .	3.2	58
53	Coulomb drag and magnetotransport in graphene double layers. Solid State Communications, 2012, 152, 1283-1288.	1.9	56
54	Lateral Spin Injection in Germanium Nanowires. Nano Letters, 2010, 10, 3297-3301.	9.1	55

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55	Coherent Interlayer Tunneling and Negative Differential Resistance with High Current Density in Double Bilayer Graphene ^{WSe₂} Heterostructures. Nano Letters, 2017, 17, 3919-3925.	9.1	53
56	Spin-Polarized to Valley-Polarized Transition in Graphene Bilayers at $\frac{1}{2}$ in High Magnetic Fields. Physical Review Letters, 2011, 107, 016803.	7.8	50
57	Bilayer Graphene-Hexagonal Boron Nitride Heterostructure Negative Differential Resistance Interlayer Tunnel FET. IEEE Electron Device Letters, 2015, 36, 405-407.	3.9	50
58	Quantum Hall effect in Bernal stacked and twisted bilayer graphene grown on Cu by chemical vapor deposition. Physical Review B, 2012, 85, .	3.2	48
59	GaAs metal-oxide-semiconductor capacitors using atomic layer deposition of HfO ₂ gate dielectric: Fabrication and characterization. Applied Physics Letters, 2007, 91, .	3.3	45
60	High-Performance Ge nMOSFETs With $\text{In}^+ \text{p}$ Junctions Formed by Spin-On Dopant. IEEE Electron Device Letters, 2011, 32, 1203-1205.	3.9	44
61	Fabrication of Self-Aligned Enhancement-Mode $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With $\text{TaN}/\text{HfO}_2/\text{AlN}$ Gate Stack. IEEE Electron Device Letters, 2008, 29, 557-560.	3.9	43
62	Anomalous spin polarization of GaAs two-dimensional hole systems. Physical Review B, 2005, 72, .	3.2	40
63	Magnetotransport Properties of Quasi-Free-Standing Epitaxial Graphene Bilayer on SiC: Evidence for Bernal Stacking. Nano Letters, 2011, 11, 3624-3628.	9.1	39
64	Intrinsic Disorder in Graphene on Transition Metal Dichalcogenide Heterostructures. Nano Letters, 2015, 15, 1925-1929.	9.1	37
65	Role of Density Imbalance in an Interacting Bilayer Hole System. Physical Review Letters, 2003, 91, 076802.	7.8	36
66	Bilayer Pseudospin Field-Effect Transistor: Applications to Boolean Logic. IEEE Transactions on Electron Devices, 2010, 57, 755-764.	3.0	36
67	Ballistic Electron Transport in AlAs Quantum Wells. Physical Review Letters, 2004, 93, 246603.	7.8	35
68	Chemical and physical interface studies of the atomic-layer-deposited Al ₂ O ₃ on GaAs substrates. Applied Physics Letters, 2008, 92, .	3.3	34
69	Role of Confinement on Carrier Transport in Si/Ge Core-Shell Nanowires. Nano Letters, 2012, 12, 108-112.	9.1	34
70	$\text{Ge-Si}_x\text{Ge}_{1-x}$ Core-Shell Nanowire Tunneling Field-Effect Transistors. IEEE Transactions on Electron Devices, 2010, 57, 1883-1888.	3.0	30
71	Negative differential Rashba effect in two-dimensional hole systems. Applied Physics Letters, 2004, 85, 3151-3153.	3.3	29
72	Spin-Conserving Resonant Tunneling in Twist-Controlled WSe_2 -hBN- WSe_2 Heterostructures. Nano Letters, 2018, 18, 5967-5973.	9.1	29

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73	Self-aligned inversion-type enhancement-mode GaAs metal-oxide-semiconductor field-effect transistor with Al ₂ O ₃ gate dielectric. Applied Physics Letters, 2008, 92, 203505.	3.3	28
74	Raman spectroscopy and strain mapping in individual Ge-Si nanowires. Physical Review B, 2012, 86, .	3.2	28
75	Effects of Electrode Layer Band Structure on the Performance of Multilayer Graphene-hBN Graphene Interlayer Tunnel Field Effect Transistors. Nano Letters, 2016, 16, 4975-4981.	9.1	28
76	Emergence of correlations in alternating twist quadrilayer graphene. Nature Materials, 2022, 21, 884-889.	27.5	28
77	Effect of oxide overlayer formation on the growth of gold catalyzed epitaxial silicon nanowires. Applied Physics Letters, 2006, 88, 103113.	3.3	27
78	Spin susceptibility of interacting two-dimensional electrons with anisotropic effective mass. Physical Review B, 2007, 76, .	3.2	26
79	Coherently Strained SiGe Core-Shell Nanowire Heterostructures. Nano Letters, 2016, 16, 392-398.	9.1	26
80	Self-aligned graphene field-effect transistors with polyethyleneimine doped source/drain access regions. Applied Physics Letters, 2012, 101, .	3.3	25
81	Enhanced-Performance Germanium Nanowire Tunneling Field-Effect Transistors Using Flash-Assisted Rapid Thermal Process. IEEE Electron Device Letters, 2010, 31, 1359-1361.	3.9	23
82	Tunable K Valley Populations in Hole-Doped Trilayer WSe_2 . Physical Review Letters, 2018, 120, 107703.	7.8	23
83	Hall mobility measurements in enhancement-mode GaAs field-effect transistors with Al ₂ O ₃ gate dielectric. Applied Physics Letters, 2010, 97, .	3.3	22
84	Improved contact resistance in ReSe ₂ thin film field-effect transistors. Applied Physics Letters, 2016, 108, .	3.3	22
85	Coulomb drag near the metal-insulator transition in two dimensions. Physical Review B, 2005, 71, .	3.2	21
86	Josephson Junction Field-Effect Transistors for Boolean Logic Cryogenic Applications. IEEE Transactions on Electron Devices, 2019, 66, 5367-5374.	3.0	20
87	In-Plane Magnetodrag between Dilute Two-Dimensional Systems. Physical Review Letters, 2003, 90, 226801.	7.8	19
88	Strong Aharonov-Bohm oscillations in GaAs two-dimensional holes. Applied Physics Letters, 2007, 90, 152104.	3.3	19
89	On the fabrication of three-dimensional silicon-on-insulator based optical phased array for agile and large angle laser beam steering systems. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C6O1-C6O7.	1.2	19
90	Critical Resistance in the AlAs Quantum Hall Ferromagnet. Physical Review Letters, 2003, 91, 216802.	7.8	18

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91	Doping of Ge _{1-x} Si _x core-shell nanowires using low energy ion implantation. Applied Physics Letters, 2008, 93, 203108.	3.3	18
92	DFT simulations of inter-graphene-layer coupling with rotationally misaligned hBN tunnel barriers in graphene/hBN/graphene tunnel FETs. Journal of Applied Physics, 2016, 120, .	2.5	18
93	Spin-Dependent Resistivity at Transitions between Integer Quantum Hall States. Physical Review Letters, 2005, 94, 176402.	7.8	17
94	Tunneling and fluctuating electron-hole Cooper pairs in double bilayer graphene. Physical Review B, 2020, 101, .	3.2	17
95	Electron mobility in monolayer WS ₂ encapsulated in hexagonal boron-nitride. Applied Physics Letters, 2021, 118, .	3.3	17
96	Oxidized Titanium as a Gate Dielectric for Graphene Field Effect Transistors and Its Tunneling Mechanisms. ACS Nano, 2014, 8, 10480-10485.	14.6	16
97	Intra-domain periodic defects in monolayer MoS ₂ . Applied Physics Letters, 2017, 110, .	3.3	16
98	Effective mass and spin susceptibility of dilute two-dimensional holes in GaAs. Physical Review B, 2011, 84, .	3.2	15
99	Enhanced Electron Mobility in Nonplanar Tensile Strained Si Epitaxially Grown on Si _x Ge _{1-x} Nanowires. Nano Letters, 2018, 18, 94-100.	9.1	15
100	Pinning Modes and Interlayer Correlation in High-Magnetic-Field Bilayer Wigner Solids. Physical Review Letters, 2007, 99, 136804.	7.8	14
101	Bulk and edge properties of twisted double bilayer graphene. Nature Physics, 2022, 18, 48-53.	16.7	14
102	Realization of an Interacting Two-Valley AlAs Bilayer System. Physical Review Letters, 2004, 92, 186404.	7.8	12
103	Measurement of carrier lifetime in micron-scaled materials using resonant microwave circuits. Nature Communications, 2019, 10, 1625.	12.8	12
104	Mean Free Path Suppression of Low-Frequency Phonons in SiGe Nanowires. Nano Letters, 2020, 20, 8384-8391.	9.1	12
105	High-mobility AlAs quantum wells with out-of-plane valley occupation. Applied Physics Letters, 2006, 89, 172118.	3.3	11
106	Atomically Resolved Elucidation of the Electrochemical Covalent Molecular Grafting Mechanism of Single Layer Graphene. Advanced Materials Interfaces, 2016, 3, 1600196.	3.7	11
107	Interlayer tunnel field-effect transistor (ITFET): physics, fabrication and applications. Journal Physics D: Applied Physics, 2017, 50, 383002.	2.8	11
108	Giant frictional drag in strongly interacting bilayers near filling factor one. Physical Review B, 2009, 79, .	3.2	10

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109	High Phosphorus Dopant Activation in Germanium Using Laser Spike Annealing. IEEE Electron Device Letters, 2016, 37, 1088-1091.	3.9	10
110	In-plane magnetic-field-induced metal-insulator transition in (311)A GaAs two-dimensional hole systems probed by thermopower. Physical Review B, 2007, 76, .	3.2	9
111	QUANTUM HALL EFFECT IN A MULTI-VALLEY TWO-DIMENSIONAL ELECTRON SYSTEM. International Journal of Modern Physics B, 2007, 21, 1388-1397.	2.0	8
112	Anomalous giant Rashba spin splitting in two-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 428-431.	2.7	7
113	Strain and Hole Gas Induced Raman Shifts in Ge/Si _x Ge _{1-x} Core-Shell Nanowires Using Tip-Enhanced Raman Spectroscopy. Nano Letters, 2015, 15, 4303-4310.	9.1	7
114	ReS ₂ -based interlayer tunnel field effect transistor. Journal of Applied Physics, 2017, 122, .	2.5	7
115	InSb pixel loaded microwave resonator for high-speed mid-wave infrared detection. Infrared Physics and Technology, 2020, 109, 103390.	2.9	7
116	Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. IEEE Transactions on Electron Devices, 2021, 68, 1524-1529.	3.0	7
117	Vertically integrated double-layer on-chip silicon membranes for 1-to-12 waveguide fanouts. Applied Physics Letters, 2012, 100, 181102.	3.3	6
118	Charge neutral counterflow transport at filling factor 1 in GaAs hole bilayers. Solid State Communications, 2007, 144, 405-408.	1.9	5
119	Shell morphology and Raman spectra of epitaxial Ge _{1-x} Si _x and Si _{1-x} Ge _x core-shell nanowires. Journal of Applied Physics, 2017, 121, 234302.	2.5	5
120	Transport spectroscopy in bilayer graphene using double layer heterostructures. 2D Materials, 2017, 4, 035018.	4.4	5
121	Magnetism and pseudo-magnetism in quantum Hall systems. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 20, 123-132.	2.7	4
122	Frictional drag between dilute two-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 300-303.	2.7	4
123	Negative Differential Resistance in Buried-Channel Ge _x C _{1-x} pMOSFETs. IEEE Electron Device Letters, 2009, 30, 136-138.	3.9	4
124	Room-Temperature Mid-Infrared Detection via Resonant Microwave Circuits. IEEE Transactions on Electron Devices, 2020, 67, 1632-1638.	3.0	4
125	Hysteretic resistance spikes at transitions between quantum Hall ferromagnets in AlAs 2D electrons. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 36-38.	2.7	3
126	Spin-dependent resistivity and quantum Hall ferromagnetism in two-dimensional electrons confined to AlAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 89-92.	2.7	3

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127	Valley susceptibility of interacting electrons and composite fermions. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2008, 40, 986-989.	2.7	3
128	Delay-Time-Enhanced Flat-Band Photonic Crystal Waveguides with Capsule-Shaped Holes on Silicon Nanomembrane. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2009, 15, 1510-1514.	2.9	3
129	Realization and Scaling of $\text{Si}_{1-x}\text{Ge}_x$ Core-Shell Nanowire n-FETs. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 4027-4033.	3.0	3
130	Strained $\text{Si}_x\text{Ge}_{1-x}$ -Ge-Si core-double-shell nanowire heterostructures for simultaneous hole and electron mobility enhancement. <i>Applied Physics Letters</i> , 2018, 113, .	3.3	3
131	Quantum Lifetime Spectroscopy and Magnetotunneling in Double Bilayer Graphene Heterostructures. <i>Physical Review Letters</i> , 2021, 127, 117701.	7.8	3
132	Fabrication of Three-Dimensional MIS Nano-Capacitor Based on Nanoimprinted Single Crystal Silicon Nanowire Arrays. <i>Micro and Nanosystems</i> , 2012, 4, 333-338.	0.6	3
133	COUNTERFLOW MEASUREMENTS IN GaAs HOLE BILAYERS: POSSIBLE EVIDENCE FOR EXCITONIC CONDENSATION. <i>International Journal of Modern Physics B</i> , 2004, 18, 3685-3692.	2.0	2
134	Zeeman splitting of interacting two-dimensional electrons with two effective masses. <i>Solid State Communications</i> , 2006, 140, 285-288.	1.9	2
135	Bilayer counterflow transport at filling factor 1 in the strong interacting regime. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 11-15.	2.7	2
136	Protein-Assembled Nanocrystal-Based Vertical Flash Memory Devices with Al ₂ O ₃ Integration. <i>Journal of Electronic Materials</i> , 2009, 38, 438-442.	2.2	2
137	Thermopower evidence for Wigner crystallization in the insulating phase of two-dimensional GaAs bilayer hole systems. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 120-123.	2.7	1
138	Wire-textured silicon solar cells. , 2010, , .		1
139	QUANTUM HALL EFFECT IN AlAs 2D ELECTRON SYSTEMS. <i>International Journal of Modern Physics B</i> , 2002, 16, 2917-2922.	2.0	0
140	Measurements of the effective g-factor in dilute GaAs 2D electrons. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 12, 420-423.	2.7	0
141	Interacting GaAs bilayer hole systems with layer density imbalance. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 22, 32-35.	2.7	0
142	Coulomb drag experiments in low density 2D hole bilayers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2006, 34, 63-68.	2.7	0
143	Capacitance analysis of wire-array solar cell. , 2010, , .		0
144	Silicon based double-layer 12 multimode interference coupler for three-dimensional photonic integration. , 2012, , .		0

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145	Germanium nMOSFETs with GeO ₂ Passivation and n+/p Junctions Formed by Spin-On Dopants. , 2012, , .		0
146	Mid-Infrared Detection using a Microwave Resonator Photoconductive Architecture. , 2019, , .		0
147	QUANTUM HALL EFFECT IN <i>AlAs</i> 2D ELECTRON SYSTEMS. , 2002, , .		0
148	COUNTERFLOW MEASUREMENTS IN <i>GaAs</i> HOLE BILAYERS: POSSIBLE EVIDENCE FOR EXCITONIC CONDENSATION. , 2005, , .		0
149	Twisted 2D electronic and photonic materials and devices. Applied Physics Letters, 2022, 120, 130401.	3.3	0